

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
150V	6.2mΩ@10V	130A

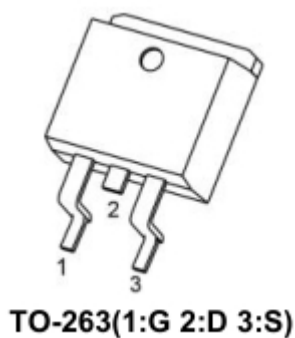
## Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

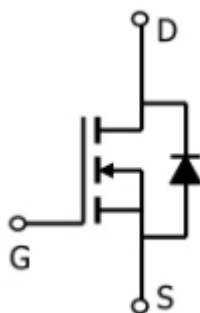
## Applications

- Power switching application
- DC-DC Converter
- Power Management

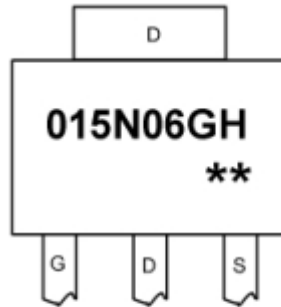
## Package



## Circuit diagram



## Marking



**015N06GH** : Product code  
**\*\*** : Week code

## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	150	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous drain current (T <sub>C</sub> = 25°C)	I <sub>D</sub>	130	W
Pulsed Drain Current	I <sub>DM</sub>	520	A
Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>D</sub>	280	W
Single Pulse Avalanche Energy <sup>1</sup>	E <sub>AS</sub>	1056	mJ
Thermal Resistance Junction- Case	R <sub>θJC</sub>	0.44	°C/ W
Operation and storage temperature	T <sub>STG</sub> , T <sub>J</sub>	-55~ +150	°C

## Electrical characteristics

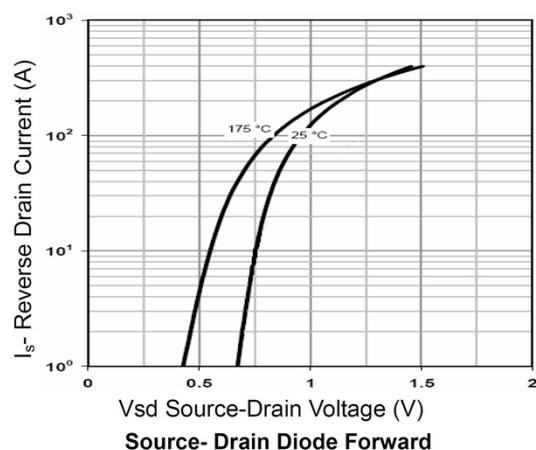
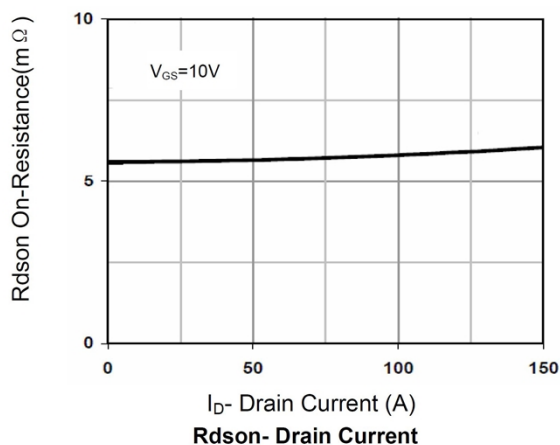
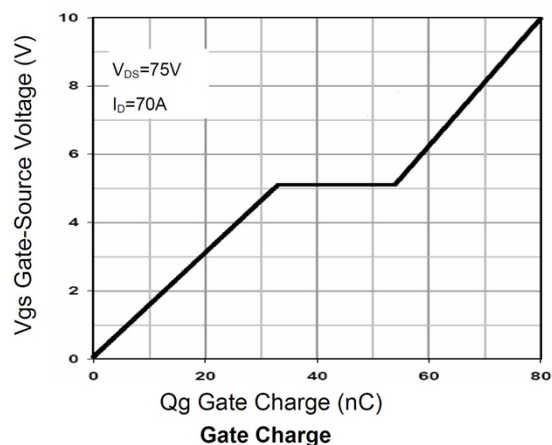
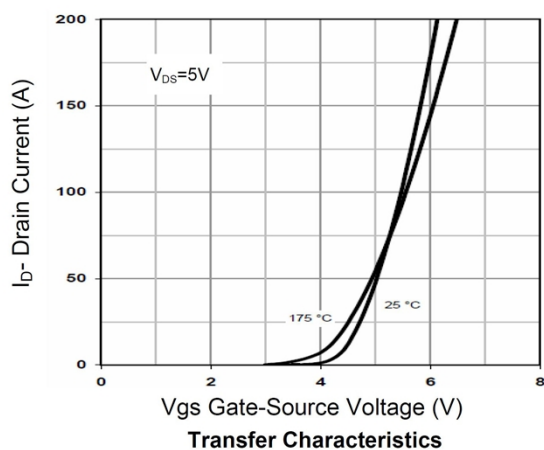
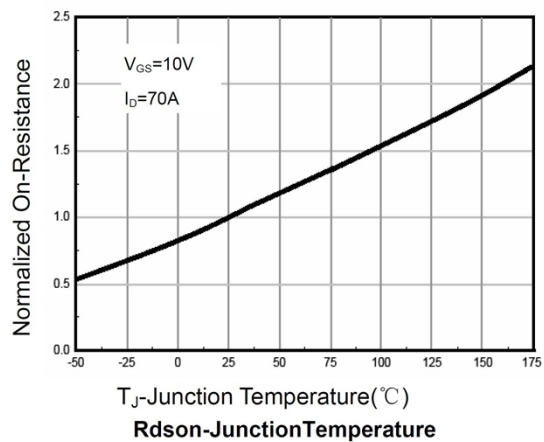
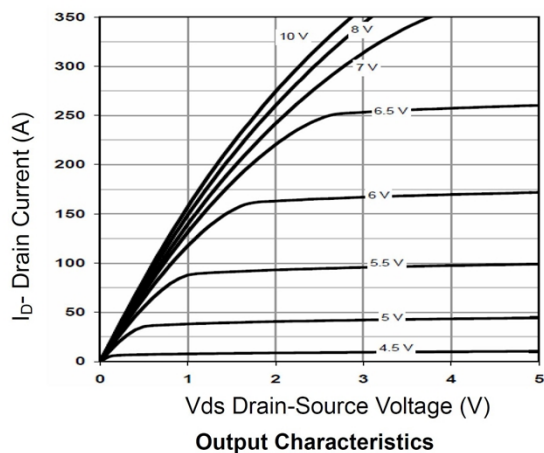
(T<sub>A</sub>=25°C, unless otherwise noted)

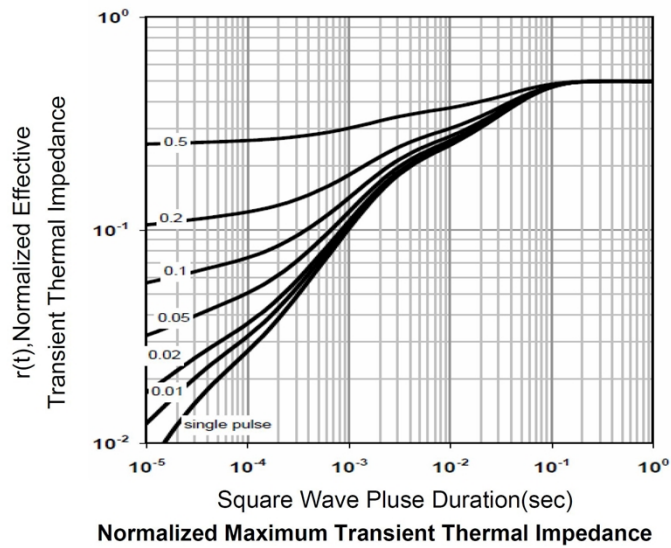
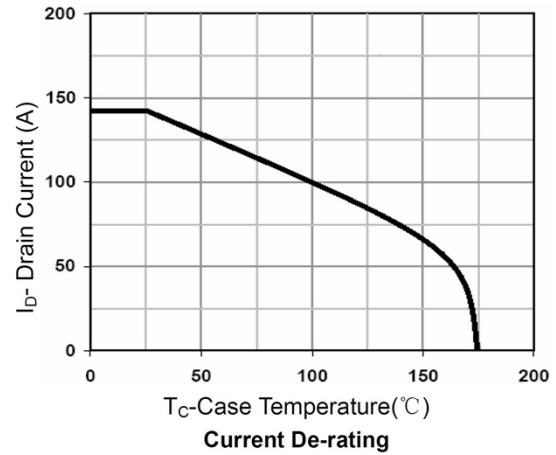
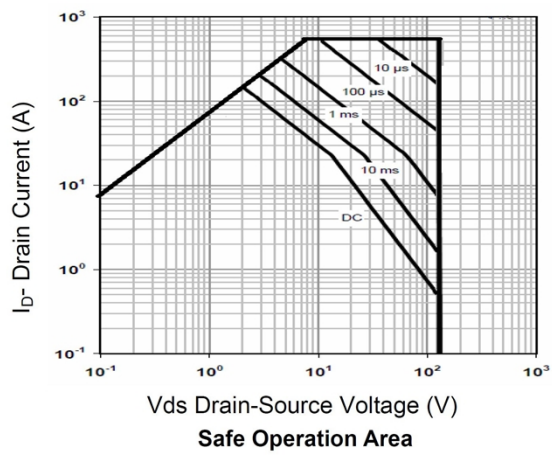
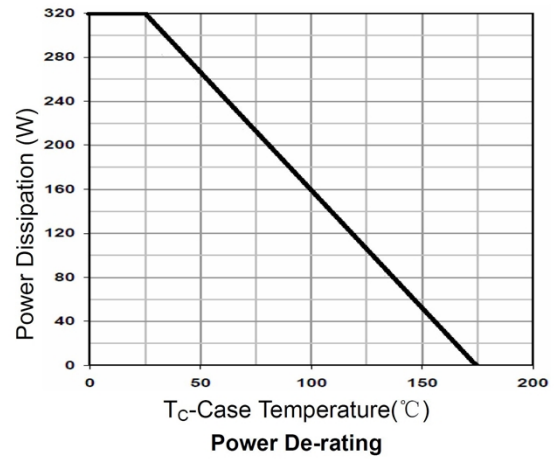
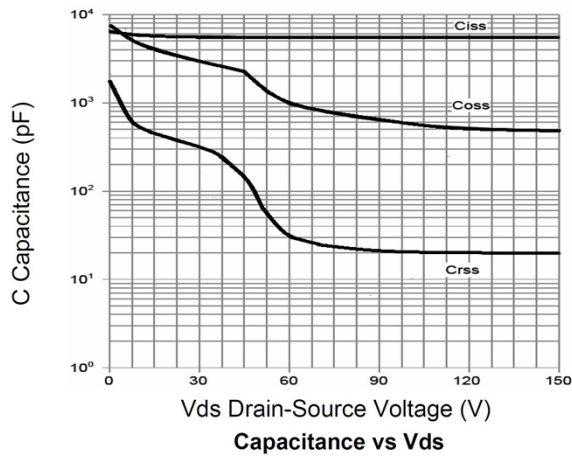
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	150			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 120V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 0.1$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	3	4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		6.2	7.5	$\Omega$
Dynamic characteristics <sup>4</sup>						
Input Capacitance	$C_{iss}$	$V_{DS} = 75V, V_{GS} = 0V, f = 1MHz$		5280		pF
Output Capacitance	$C_{oss}$			653		
Reverse Transfer Capacitance	$C_{rss}$			24		
Switching Characteristics						
Total Gate Charge(4.5V)	$Q_g$	$V_{DS} = 75V, V_{GS} = 10V, I_D = 70A$		80		nC
Gate-Source Charge	$Q_{gs}$			33		
Gate-Drain Charge	$Q_{gd}$			21		
Turn-On Delay Time	$T_{d(on)}$	$V_{GS} = 10V, V_{DS} = 75V, R_L = 3\Omega, R_G = 4.7\Omega$		26		nS
Rise Time	$T_r$			35		
Turn-Off Delay Time	$T_{d(off)}$			45		
Fall Time	$T_f$			17		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	$V_{SD}$	$I_S = 1A, V_{GS} = 0V$			1.2	V

### Note :

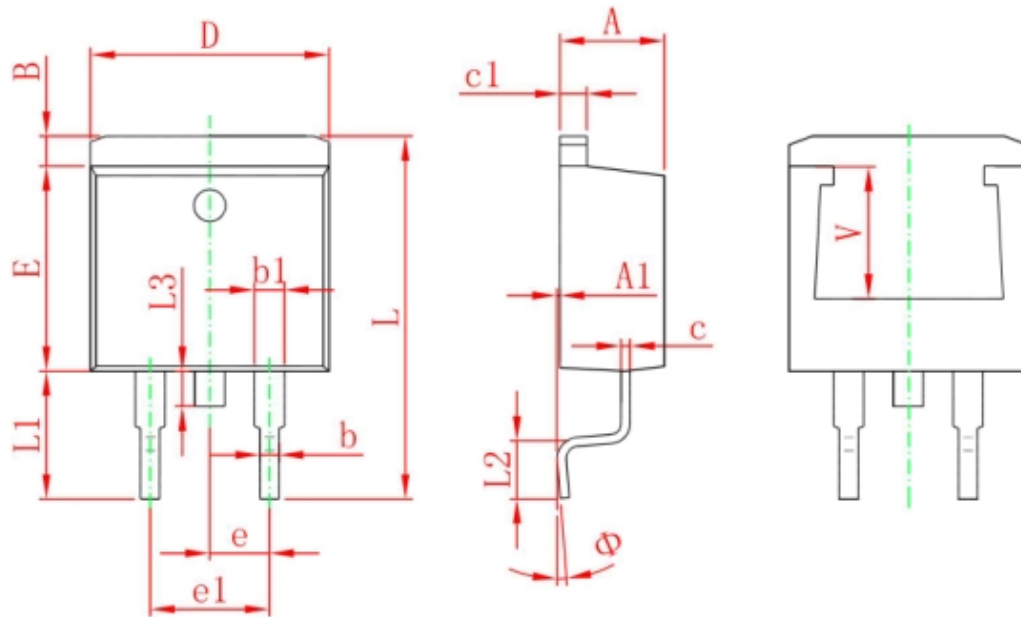
1. E<sub>AS</sub> is tested at starting T<sub>j</sub> = 25°C, V<sub>DD</sub> = 75V, V<sub>GS</sub> = 10V, L = 0.5mH, R<sub>G</sub> = 25Ω ;

## Typical Characteristics





## TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220 REF.	